1SS227

Silicon Epitaxial Planar Type

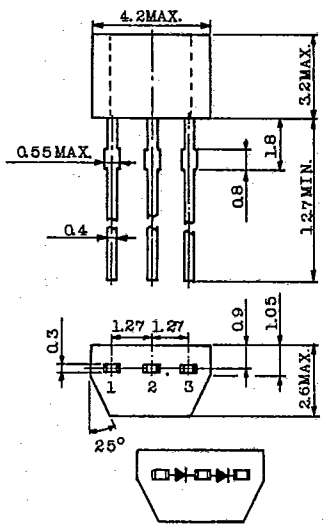
Diode

ULTRA HIGH SPEED SWITCHING APPLICATION.

FEATURES:

- Low Forward Voltage : V_F=0.9V (Typ.)
- Fast Reverse Recovery Time : t_{rr}=1.6ns (Typ.)
- Small Total Capacitance : C_T=0.9pF (Typ.)

Unit in mm



1. ANODE 1
2. CATHODE 1/ ANODE 2
3. CATHODE 2

JEDEC	—
EIAJ	—
TOSHIBA	1-4E2C

Weight : 0.13g

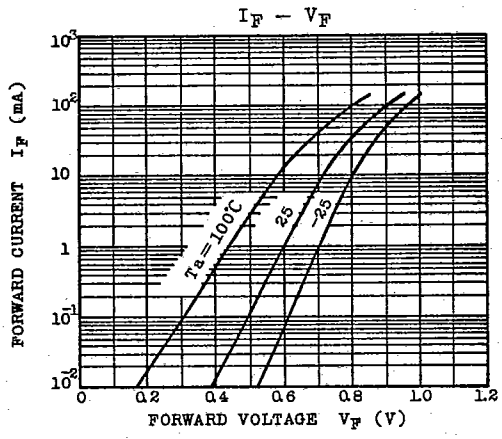
MAXIMUM RATINGS (Ta=25°C)

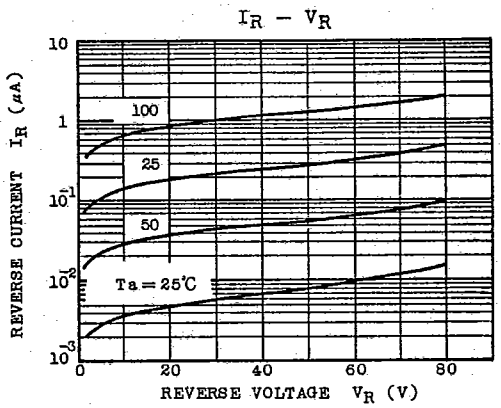
CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum(Peak) Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V_R	80	V
Maximum(Peak) Forward Current	I_{FM}	300※	mA
Average Forward Current	I_O	100※	mA
Surge Current (10ms)	I_{FSM}	2※	A
Power Dissipation	P	200	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	-55～125	°C

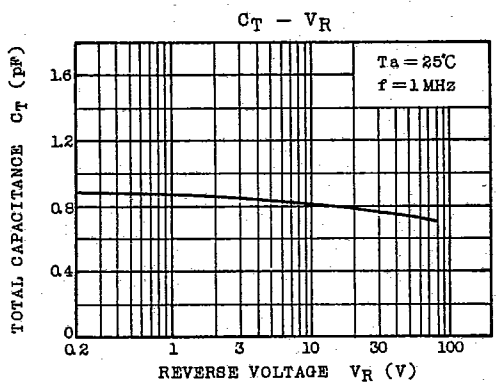
※ Unit Rating. Total Rating=Unit Rating × 0.7

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_{F(1)}$	I_F=1mA	-	0.60	-	V
	$V_{F(2)}$	I_F=10mA	-	0.72	-	
	$V_{F(3)}$	I_F=100mA	-	0.90	1.20	
Reverse Current	$I_{R(1)}$	V_R=30V	-	-	0.1	μA
	$I_{R(2)}$	V_R=80V	-	-	0.5	
Total Capacitance	C_T	V_R=0, f=1MHz	-	0.9	3.0	pF
Reverse Recovery Time	t_{rr}	I_F=10mA, Fig.1	-	1.6	4.0	ns







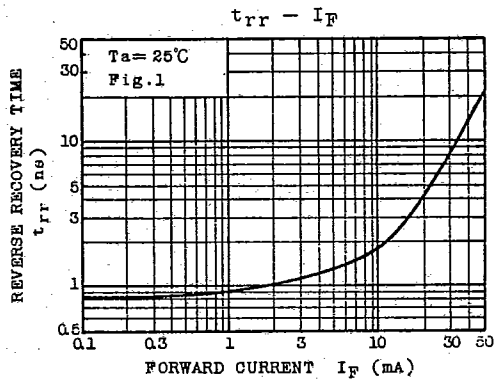
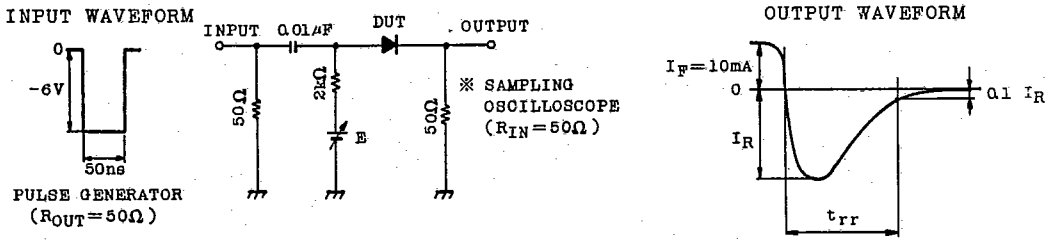



Fig 1 REVERSE RECOVERY TIME (t_{rr}) TEST CIRCUIT